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Renesas Technology Corp. Customer Support Dept. April 1, 2003



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# **HVD133**

Silicon Epitaxial Planar Pin Diode for High Frequency Switching



ADE-208-947 (Z)

Rev. 0 Jun. 2000

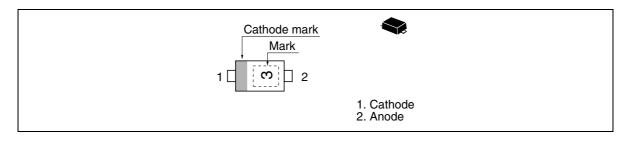
#### **Features**

- Low capacitance.(C1 = 1.0 pF max)
- Low forward resistance. (rf =  $0.7 \Omega \text{ max}$ )
- Super small Flat Package (SFP) is suitable for surface mount design.

### **Ordering Information**

Type No.	Laser Mark	Package Code
HVD133	3	SFP

## Pin Arrangement



## **HVD133**

# **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Value	Unit	Unit	
Reverse voltage	V <sub>R</sub>	30	V		
Power dissipation	Pd	150	mW		
Junction temperature	Tj	125	°C		
Storage temperature	Tstg	−55 to +125	°C		

#### **Electrical Characteristics**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Min	Тур	Max	Unit	Test Condition
Reverse voltage	$V_{_{R}}$	30	_	_	٧	I <sub>R</sub> = 1 μA
Reverse current	I <sub>R</sub>	_	_	100	nA	V <sub>R</sub> = 25 V
Forward voltage	V <sub>F</sub>	_	_	0.85	٧	I <sub>F</sub> = 2 mA
Capacitance	C <sub>1</sub>	_	_	1.0	pF	V <sub>R</sub> = 1 V, f = 1 MHz
	C <sub>6</sub>	_	_	0.9		V <sub>R</sub> = 6 V, f = 1 MHz
Forward resistance	r,	_	0.55	0.7	Ω	I <sub>F</sub> = 2 mA, f = 100 MHz

Note: Please do not use the soldering iron due to avoid high stress to the SFP package.

#### **Main Characteristic**

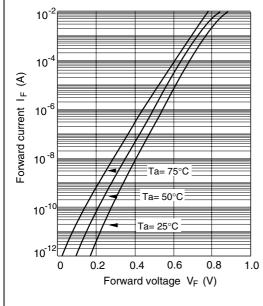


Fig.1 Forward current Vs. Forward voltage

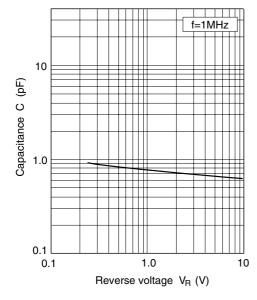


Fig.3 Capacitance Vs. Reverse voltage

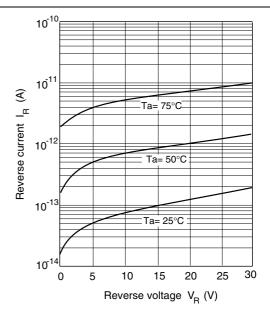


Fig.2 Reverse current Vs. Reverse voltage

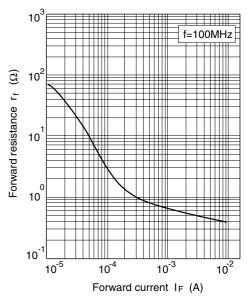
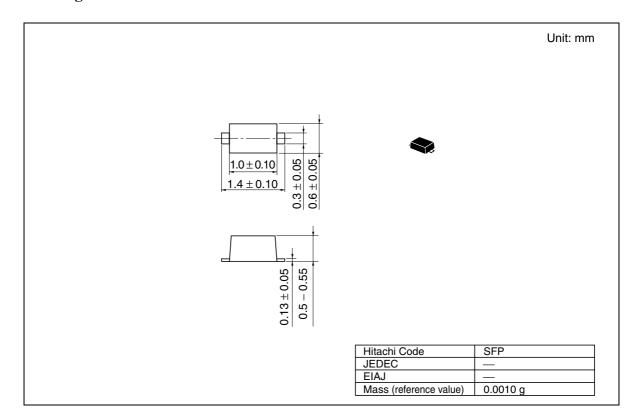


Fig.4 Forward resistance Vs. Forward current

# **HVD133**

# **Package Dimensions**



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